

KHX12800D3/1G

1GB 128M x 64-Bit PC3-12800

CL9 240-Pin DIMM

DESCRIPTION:

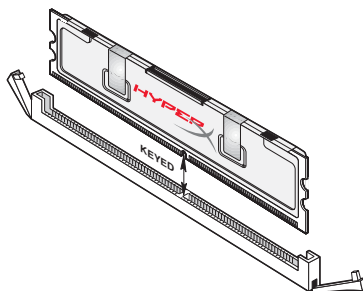
This document describes Kingston's 128M x 64-bit 1GB (1024MB) DDR3-1600 CL9 SDRAM (Synchronous DRAM) memory module, based on eight 128M x 8-bit DDR3 FBGA components. This module has been tested to run at DDR3-1600MHz at a low latency timing of 9-9-9-27 at 1.7V to 1.9V. The SPD is programmed to JEDEC standard latency DDR3-1066Mhz timing of 7-7-7-20 at 1.5V. This 240-pin DIMM uses gold contact fingers and requires +1.5V. The JEDEC standard electrical and mechanical specifications are as follows:

FEATURES:

- ✓ JEDEC standard 1.5V $\pm$ 0.075V Power Supply
- ✓ VDDQ = 1.5V $\pm$ 0.075V
- ✓ 533MHz fCK for 1066Mb/sec/pin
- ✓ 8 independent internal bank
- ✓ Programmable CAS Latency: 6,7,8,9,10
- ✓ Posted CAS
- ✓ Programmable Additive Latency: 0, CL - 2, or CL - 1 clock
- ✓ Programmable CAS Write Latency(CWL) = 7(DDR3-1066)
- ✓ 8-bit pre-fetch
- ✓ Burst Length: 8 (Interleave without any limit, sequential with starting address "000" only), 4 with tCCD = 4 which does not allow seamless read or write [either on the fly using A12 or MRS]
- ✓ Bi-directional Differential Data Strobe
- ✓ Internal(self) calibration : Internal self calibration through ZQ pin (RZQ : 240 ohm $\pm$ 1%)
- ✓ On Die Termination using ODT pin
- ✓ Average Refresh Period 7.8us at lower then TCASE 85°C, 3.9us at 85°C < TCASE . 95°C
- ✓ Asynchronous Reset
- ✓ 1066Mbps CL7 doesn't have backward compatibility with 800Mbps CL5
- ✓ PCB : Height 1.180" (30.00mm), single sided component

PERFORMANCE:

- | | |
|--|-------------------|
| ✓ CL(IDD) | 7 cycles |
| ✓ Row Cycle Time (tRCmin) | 50.625ns (min.) |
| ✓ Refresh to Active/Refresh Command Time (tRFCmin) | 110ns |
| ✓ Row Active Time (tRASmin) | 37.5ns (min.) |
| ✓ Power | TBD W (operating) |
| ✓ UL Rating | 94 V - 0 |
| ✓ Operating Temperature | 0° C to 85° C |
| ✓ Storage Temperature | -55° C to +100° C |



MODULE DIMENSIONS: